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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/666,988	09/18/2003	John C. Rudelic	ITL.0602C1US (P11743C)	6661
7.	590 03/18/2004		EXAM	NER
Timothy N. Trop TROP, PRUNER & HU, P.C.			TRAN, MICHAEL THANH	
STE 100	ER & HU, P.C.	ART UNIT	PAPER NUMBER	
8554 KATY FWY, HOUSTON, TX 77024-1805			2818	
			DATE MAILED: 03/18/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
Office Action Summary		10/666,988	RUDELIC ET AL.			
		Examiner	Art Unit			
		Michael T Tran	2818			
Period f	The MAILING DATE of this communication apports.	pears on the cover sheet	with the correspondence address			
THE - Extended - If th - If No - Fail Any	HORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. ensions of time may be available under the provisions of 37 CFR 1.1 r SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a repl O period for reply is specified above, the maximum statutory period ure to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may by within the statutory minimum of the will apply and will expire SIX (6) Monday, cause the application to become	a reply be timely filed hirty (30) days will be considered timely. DNTHS from the mailing date of this communication. ABANDONED (35 U.S.C. § 133).			
Status						
1)[🛛	Responsive to communication(s) filed on 18 S	September 2003.				
2a)□	This action is FINAL . 2b) This action is non-final.					
3)□						
	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Disposi	tion of Claims					
4)⊠	Claim(s) <u>1-8,10-16 and 18-20</u> is/are pending in the application.					
·	4a) Of the above claim(s) is/are withdrawn from consideration.					
5)□	Claim(s) is/are allowed.					
6)⊠	Claim(s) <u>1-3,7,8 and 13-16</u> is/are rejected.					
7)🖂	Claim(s) <u>4-6,10-12 and 18-20</u> is/are objected to.					
8)□	Claim(s) are subject to restriction and/o	or election requirement.				
Applica	tion Papers					
9)[The specification is objected to by the Examina	er.				
10)	The drawing(s) filed on is/are: a)☐ acc	cepted or b) objected t	o by the Examiner.			
	Applicant may not request that any objection to the	drawing(s) be held in abey	ance. See 37 CFR 1.85(a).			
	Replacement drawing sheet(s) including the correct	tion is required if the drawi	ng(s) is objected to. See 37 CFR 1.121(d).			
11)	The oath or declaration is objected to by the E	xaminer. Note the attach	ed Office Action or form PTO-152.			
Priority	under 35 U.S.C. § 119					
а	Acknowledgment is made of a claim for foreign All b Some * c None of: 1. Certified copies of the priority documen 2. Certified copies of the priority documen 3. Copies of the certified copies of the priority documen application from the International Burea See the attached detailed Office action for a list	ts have been received. ts have been received in ority documents have bea ou (PCT Rule 17.2(a)).	Application No en received in this National Stage			
		1 1				
Attachme	nt(s)	\mathcal{M}				
	ice of References Cited (PTO-892)		w Summary (PTO-413)			
	ice of Draftsperson's Patent Drawing Review (PTO-948) ormation Disclosure Statement(s) (PTO-1449 or PTO/SB/08		lo(s)/Mail Date of Informal Patent Application (PTO-152)			
	per No(s)/Mail Date	6) 🔲 Other: _				

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DETAILED ACTION

In response to the Communications dated September 18, 2003, claims 1-8, 10
 and 18-20 are active in this application as a result of the cancellation of claims 9
 and 17.

Claim Objections

2. Claims 4-6, 10-12, and 18-20 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

It appears that the recitations of claim 3 has already been introduced in claim 1; hence, claim 3 should be deleted.

Claim Rejections - 35 U.S.C. § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in-
- (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effect under this subsection of a national application published under section 122(b) only if the international application designating the United States was published under Article 21(2)(a) of such treaty in the English language; or
- (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that a patent shall not be deemed filed in the United States for the

purposes of this subsection based on the filing of an international application filed under the treaty defined in section 351(a).

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4. Claims 1-3 are rejected under 35 U.S.C 102(b) as being anticipated by Lu et al. [U.S. Patent #6,215,697].

With respect to claim 1, Lu et al. disclose a method comprising: storing data at a first density in a first cell in a first memory array [see 2nd paragraph of the "Description of Related Art]; storing data at a second density in a second cell in the first memory array [see 2nd paragraph of the "Description of Related Art]; and dynamically changing the number of bits stored per cell [see 1st paragraph of the "Description of Related Art]. In the cited paragraphs, Lu et al. indicated that different memory cells within an array of memory cells can be programmed to store different densities [multiple levels]. Additionally, Lu et al. also indicated that the memory cells can be dynamically altered [reprogrammed] into another level.

With respect to claim 2, Lu et al. diclose a method wherein storing data at a second density in a second cell includes storing fewer bits per cell in one of said first or second cells [see 2nd paragraph of the "Description of Related Art]. As stated above, in the cited paragraphs, Lu et al. indicated that different memory cells within an array of memory cells can be programmed to store different densities [multiple levels]. Depending on a situation, one cell can be programmed with more levels than another within the same array of memory cells.

With respect to claim 3, it appears that the recitations for this claim have already been established in claim 1.

5. Claims 7 and 8 are rejected under 35 U.S.C 102(b) as being anticipated by Lu et al. [U.S. Patent #6,215,697].

With respect to claim 7, Lu et al. disclose an article comprising a medium storing instructions, that, if executed, enable a processor-based system [see 1st paragraph of the "Description of Related Art] to: store data at a first density in a first cell in a first memory [see 2nd paragraph of the "Description of Related Art]; store data at a second density in a second cell in said first memory array [see 2nd paragraph of the "Description of Related Art]; and dynamically change the number of bits stored per cell [see 1st paragraph of the "Description of Related Art]. In the cited sections, Lu et al. indicated that there exists a device applicable to a computer, which is a processor-based system, having the capability to store different densities in different memory cells within an array of memory cells. Lu et al. further indicated, in the cited sections, that the stored densities can be dynamically altered [reprogrammed] to other levels.

With respect to claim 8, Lu et al. disclose a device further storing instructions that enable the processor-based system to store fewer bits per cell in one of said first or second cells [see 2nd paragraph of the "Description of Related Art]. As stated above, in the cited paragraphs, Lu et al. indicated that different memory cells within an array of memory cells can be programmed to store different densities [multiple levels]. Depending on a situation, one cell can be programmed with more levels than another within the same array of memory cells.

6. Claims 13-16 are rejected under 35 U.S.C 102(b) as being anticipated by Lu et al. [U.S. Patent #6,215,697].

With respect to claim 13, Lu et al. disclose a memory comprising: a memory array including a first and second cell [see 2nd paragraph of the "Description of Related Art]; and a controller coupled to said array to store data in said array at a first density in the first cell and to store data at a second density in the second cell wherein said controller to dynamically change the number of bits stored per cell [see 1st and 2nd paragraph of the "Description of Related Art]. In the cited sections, Lu et al. indicated that there exists a device applicable to a computer, which is a processor-based system, having the capability to store different densities in different memory cells within an array of memory cells. Lu et al. further indicated, in the cited sections, that the stored densities can be dynamically altered [reprogrammed] to other levels.

Furthermore, since Lu et al. indicated that the device is applicable to a computer, it is therefore reasonable to assume that there exists a controller to initiate commands to perform particular functions such as reprogramming, programming, reading, etc.

With respect to claim 14, Lu et al. indicated that the memory, as claimed, is a flash memory [see 2nd paragraph of the "Description of Related Art].

With respect to claim 15, Lu et al. indicated that the memory is a multi-level cell memory [see 1st and 2nd paragraph of the "Description of Related Art].

With respect to claim 16, Lu et al. disclose said controller stores fewer bits per cell in one of said first or second cells [see 1st and 2nd paragraph of the "Description of Related Art]. As stated above, in the cited paragraphs, Lu et al. indicated that

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different memory cells within an array of memory cells can be programmed to store different densities [multiple levels]. Depending on a situation, one cell can be programmed with more levels than another within the same array of memory cells. Furthermore, since Lu et al. indicated that the device is applicable to a computer, it is therefore reasonable to assume that there exists a controller to initiate commands to perform particular functions such as reprogramming, programming, reading, etc.

Allowable Subject Matter

- 7. The following is an Examiner's statement of reasons for the indication of allowable subject matter: the prior art of records does not show (in addition to the other elements in the claim) the following:
 - A method of storing data at levels that are spaced from one another in a cell in order to improve the read fidelity.
 - A method of storing data in regularly spaced levels within a cell while leaving intervening levels within the cell unoccupied by stored data.

Conclusion

- 8. When responding to the Office action, Applicants are advised to provide the Examiner with line and page numbers of the application and/or references cited to assist the Examiner in the prosecution of this case.
 - 9. Any inquiry concerning this communication or earlier communications from

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the Examiner should be directed to Michael T. Tran whose telephone number is (571) 272-1795. The Examiner can normally be reached on Monday-Thursday from 7:30-6:00 P.M.

10. Any inquiry of a general nature or relating to the status of this application should be directed to the Group receptionist whose telephone number is (571) 272-1650.

Michael T. Tran Art Unit 2818 March 12, 2004